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Vishay Semiconductor/Diodes Division VS-HFA06PB120PBF

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Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite

Datasheet of VS-HFA06PB120PBF - DIODE GEN PURP 1.2KV 6A TO247AC Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



VS-HFA06PB120PbF, VS-HFA06PB120-N3

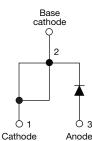
Vishay Semiconductors

HEXFRED[®], Ultrafast Soft Recovery Diode, 6 A



www.vishay.com

TO-247AC modified



PRODUCT SUMMARY									
Package	TO-247AC modified (2 pins)								
I _{F(AV)}	6 A								
V _R	1200 V								
V _F at I _F	2.4 V								
t _{rr} typ.	26 ns								
T _J max.	150 °C								
Diode variation	Single die								

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{BBM} and Q_{rr}
- Designed and qualified according to JEDEC[®]-JESD47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA06PB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 6 A continuous current, the VS-HFA06PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA06PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Cathode to anode voltage	V _R		1200	V						
Maximum continuous forward current	I _F	T _C = 100 °C	6							
Single pulse forward current	I _{FSM}		80	А						
Maximum repetitive forward current	I _{FRM}		24							
Maximum power dissinction	Р	T _C = 25 °C	62.5	W						
Maximum power dissipation	P _D	T _C = 100 °C	25	vv						
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C						

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ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-					
Maximum forward voltage	V _{FM}	I _F = 6.0 A	-	2.7	3.0	v				
		I _F = 12 A	-	3.5	3.9					
		I _F = 6.0 A, T _J = 125 °C	-	2.4	2.8					
Maximum reverse		$V_{R} = V_{R}$ rated	-	0.26	5.0					
leakage current	I _{RM}	T_J = 125 °C, V_R = 0.8 x V_R rated	-	110	500	μA				
Junction capacitance	CT	V _R = 200 V	-	9.0	14	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH				

DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time	t _{rr}	I _F = 1.0 A, dI _F /dt = 200	A/ μ s, V _R = 30 V	-	26	-	ns A			
	t _{rr1}	T _J = 25 °C		-	53	80				
	t _{rr2}	T _J = 125 °C		-	87	130				
Deels receiver a current	I _{RRM1}	T _J = 25 °C		-	4.4	8.0				
Peak recovery current	I _{RRM2}	T _J = 125 °C	l _F = 6.0 A dl _F /dt = 200 A/μs	-	5.0	9.0				
	Q _{rr1}	T _J = 25 °C	$V_{\rm R} = 200 \text{ V}$	-	116	320				
Reverse recovery charge	Q _{rr2}	T _J = 125 °C		-	233	585	ne			
Peak rate of recovery current during $t_{\rm b}$	dl _{(rec)M} /dt1	T _J = 25 °C		-	180	-	A∕µs			
	dl _{(rec)M} /dt2	T _J = 125 °C		-	100	-	Ανμs			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	2.0					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-					
Woight			-	2.0	-	g				
Weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-247AC modified		HFA06	PB120					

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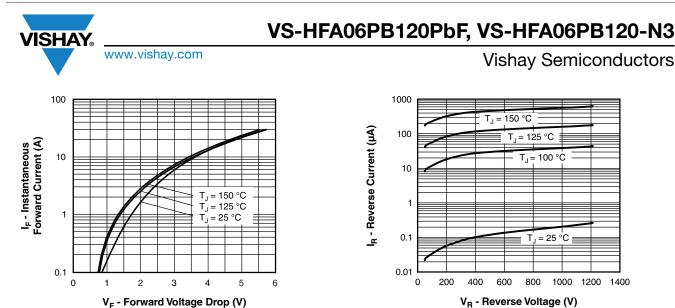
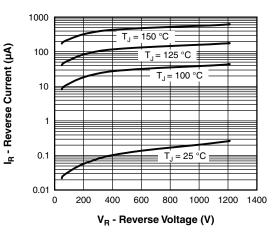


Fig. 1 - Typical Forward Voltage Drop Characteristics



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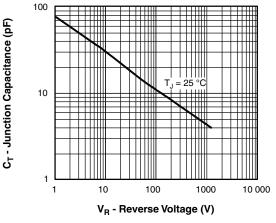
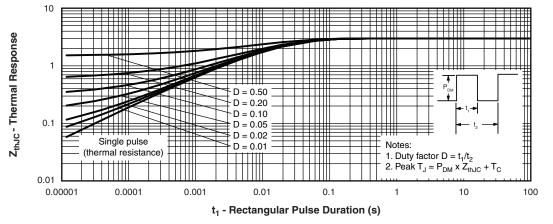


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





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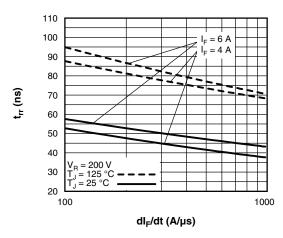


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Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

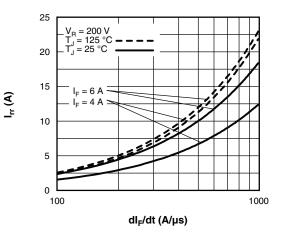


Fig. 6 - Typical Recovery Current vs. dl_F/dt

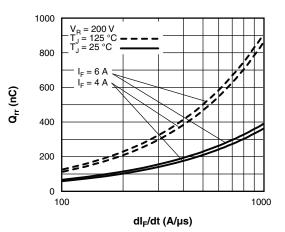


Fig. 7 - Typical Stored Charge vs. dl_F/dt

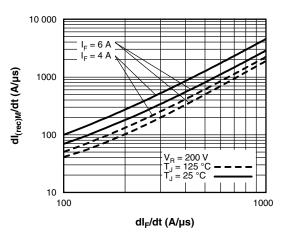


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

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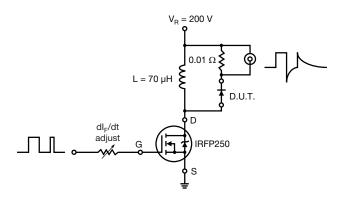


Fig. 9 - Reverse Recovery Parameter Test Circuit

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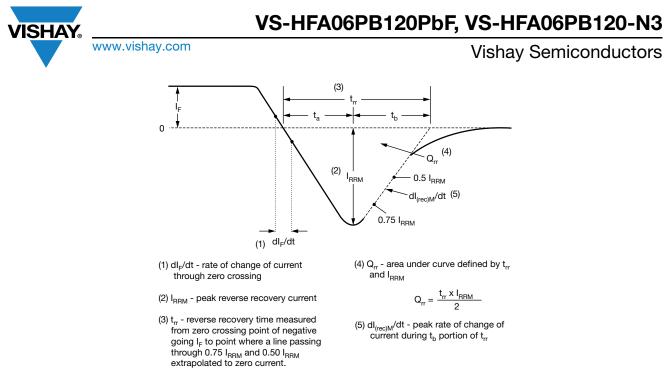
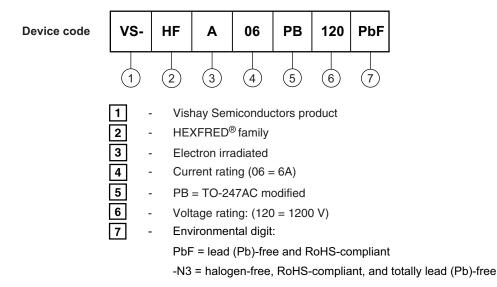


Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-HFA06PB120PbF	25	500	Antistatic plastic tube							
VS-HFA06PB120-N3	25	500	Antistatic plastic tube							

LINKS TO RELATED DOCUMENTS								
Dimensions		www.vishay.com/doc?95541						
Part marking information	TO-247AC modified PbF	www.vishay.com/doc?95255						
	TO-247AC modified -N3	www.vishay.com/doc?95442						

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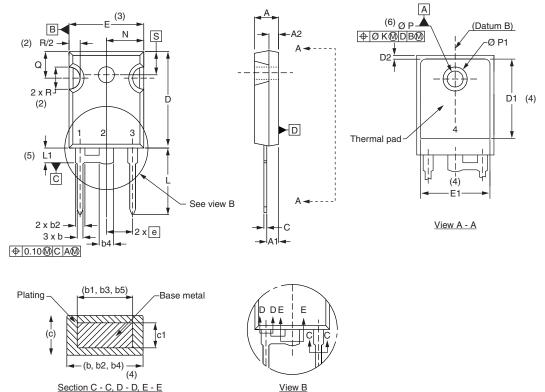


Outline Dimensions

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TO-247 modified

DIMENSIONS in millimeters and inches



Section	С	-	C,	D	-	D,	Е	-	Е

SYMBOL	MILLIN	IETERS	INC	HES	NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWBOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.65	5.31	0.183	0.209			D2	0.51	1.30	0.020	0.051	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.50	2.49	0.059	0.098			E1	13.72	-	0.540	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ØК	2.	54	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			N	7.62	BSC	0	.3	
b5	2.59	3.38	0.102	0.133			ØΡ	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	-	6.98	-	0.275	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3]	R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	' BSC	

Notes

⁽¹⁾ Dimensioning and tolerance per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

(5) Lead finish uncontrolled in L1

(6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

(7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c

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